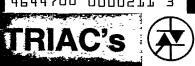
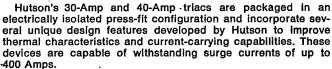
## TSON INDUSTRIES





**30 AMPERE CENTER GATE 40 AMPERE CENTER GATE** 

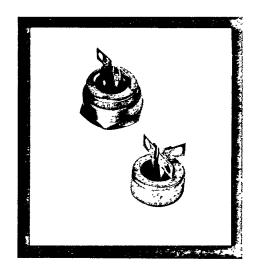


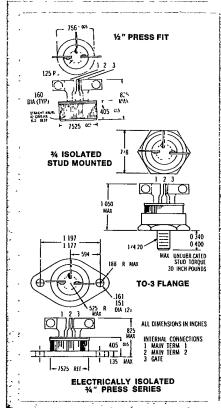
Construction features include extra-heavy main terminals 1, 2 and gate leads. These leads are extended to the end of the header terminals and are crimped and welded with the header tubes, providing a superior electrical connection. Beryllium oxide is used as a substrate for the chip in order to provide electrical isolation. A molybdenum stress reliever, between the chip and substrate, reduces the shear forces generated by cycling for improved thermal characteristics. Molybdenum is also used as a current spreader for Main Terminal No. 1.

In the chip Itself, shorted emitter and center gate construction are used to improve critical and commutating dv/dt ratings and di/dt capabilities. Chips are protected by Hutson's pat-ented inorganic passivation technique using a proprietary, extremely dense void-free glass in a dual-mesa configuration. Chips are hermetically sealed and electrically isolated from the package. Package is also hermetically sealed.

These Hutson triacs are bidirectional triode thyristors which may be switched from off-state to conduction for either polarity of applied voltage with positive or negative gate triggering. They are designed for control of AC loads in applications such as lighting, heating, and motor speed controls, and static switching relays.

Hutson manufactures a complete line of triacs in standard package configurations, from 3 Ampere to 60 Ampere ratings. All Hutson triacs are also available in chip form.





## **HUTSON INDUSTRIES**

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